

## BB301M

Built in Biasing Circuit MOS FET IC  
VHF RF Amplifier

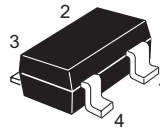
REJ03G0824-0300  
(Previous ADE-208-506A)  
Rev.3.00  
Aug.10.2005

### Features

- Built in Biasing Circuit; To reduce using parts cost & PC board space.
- Low noise characteristics;  
(NF = 1.3 dB typ. at f = 200 MHz)
- Withstanding to ESD;  
Built in ESD absorbing diode. Withstand up to 200V at C=200pF, Rs=0 conditions.
- Provide mini mold packages; MPAK-4(SOT-143Rmod)

### Outline

RENESAS Package code: PLSP0004ZA-A  
(Package name: MPAK-4)



1. Source
2. Gate1
3. Gate2
4. Drain

- Notes:
1. Marking is "AW-".
  2. BB301M is individual type number of RENESAS BBFET.

## Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DS}$	6	V
Gate1 to source voltage	$V_{G1S}$	+6 -0	V
Gate2 to source voltage	$V_{G2S}$	±6	V
Drain current	$I_D$	25	mA
Channel power dissipation	Pch	150	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

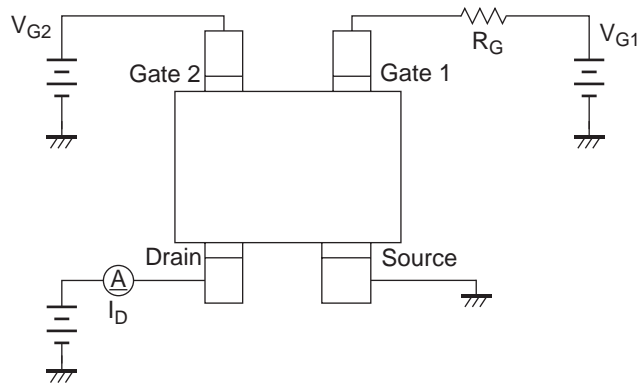
## Electrical Characteristics

(Ta = 25°C)

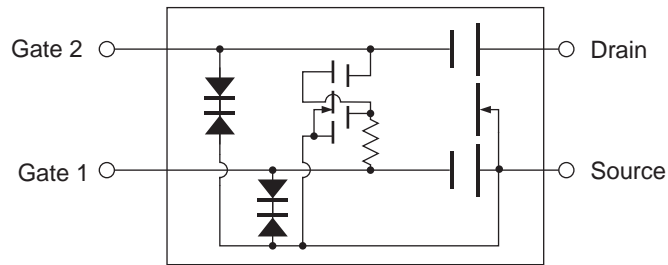
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	6	—	—	V	$I_D = 200 \mu A, V_{G1S} = V_{G2S} = 0$
Gate1 to source breakdown voltage	$V_{(BR)G1SS}$	+6	—	—	V	$I_{G1} = +10 \mu A, V_{G2S} = V_{DS} = 0$
Gate2 to source breakdown voltage	$V_{(BR)G2SS}$	±6	—	—	V	$I_{G2} = \pm 10 \mu A, V_{G1S} = V_{DS} = 0$
Gate1 to source cutoff current	$I_{G1SS}$	—	—	+100	nA	$V_{G1S} = +5 V, V_{G2S} = V_{DS} = 0$
Gate2 to source cutoff current	$I_{G2SS}$	—	—	±100	nA	$V_{G2S} = \pm 5 V, V_{G1S} = V_{DS} = 0$
Gate1 to source cutoff voltage	$V_{G1S(off)}$	0.4	—	1.0	V	$V_{DS} = 5 V, V_{G2S} = 4 V$ $I_D = 100 \mu A$
Gate2 to source cutoff voltage	$V_{G2S(off)}$	0.4	—	1.0	V	$V_{DS} = 5 V, V_{G1S} = 5 V$ $I_D = 100 \mu A$
Drain current	$I_{D(op)}$	10	15	20	mA	$V_{DS} = 5 V, V_{G1} = 5 V$ $V_{G2S} = 4 V, R_G = 100 k\Omega$
Forward transfer admittance	$ y_{fs} $	15	20	—	mS	$V_{DS} = 5 V, V_{G1} = 5 V, V_{G2S} = 4 V$ $R_G = 100 k\Omega, f = 1 kHz$
Input capacitance	Ciss	2.2	3.0	3.9	pF	$V_{DS} = 5 V, V_{G1} = 5 V$
Output capacitance	Coss	0.9	1.2	1.6	pF	$V_{G2S} = 4 V, R_G = 100 k\Omega$
Reverse transfer capacitance	Crss	—	0.018	0.04	pF	$f = 1 MHz$
Power gain	PG	22	26	—	dB	$V_{DS} = 5 V, V_{G1} = 5 V, V_{G2S} = 4 V$
Noise figure	NF	—	1.3	1.9	dB	$R_G = 100 k\Omega, f = 200 MHz$

Main Characteristics

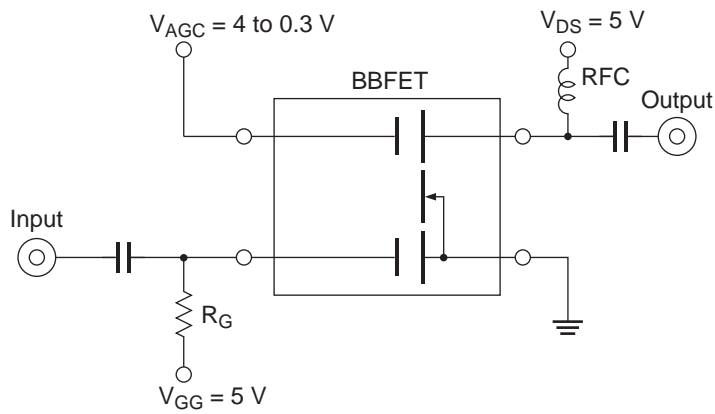
Test Circuit for Operating Items ( $I_{D(op)}$ ,  $|y_{fs}|$ ,  $C_{iss}$ ,  $C_{oss}$ ,  $C_{rss}$ ,  $NF$ ,  $PG$ )



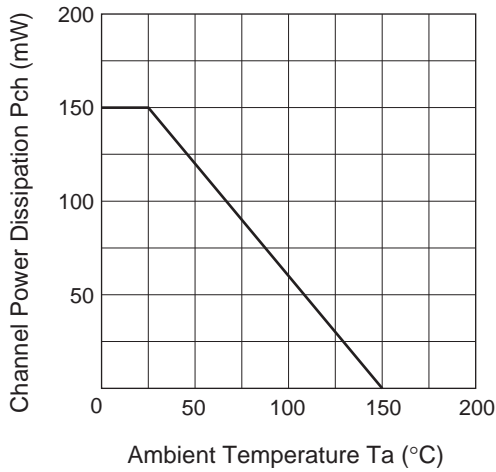
Equivalent Circuit



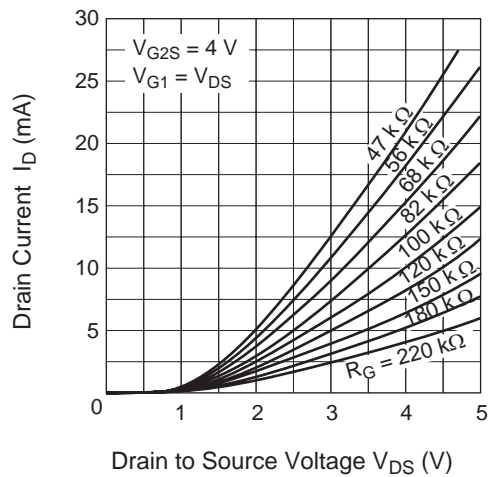
Application Circuit



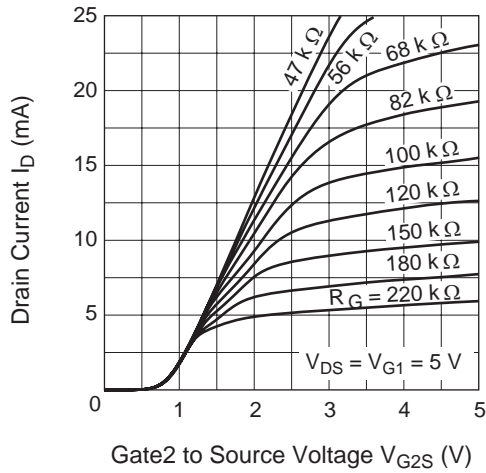
Maximum Channel Power Dissipation Curve



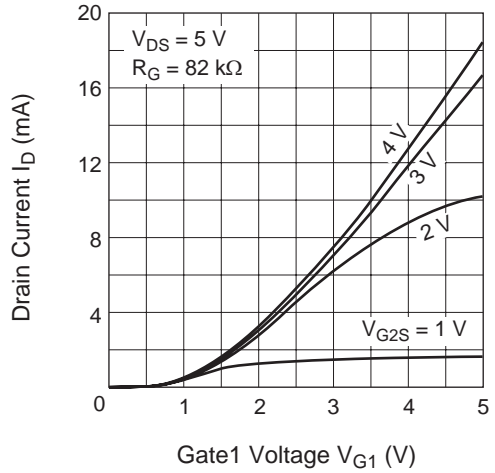
Typical Output Characteristics



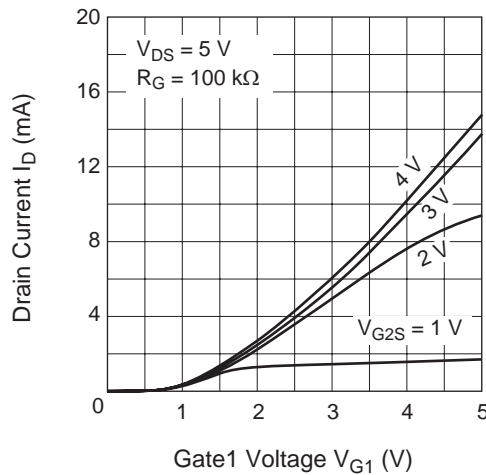
Drain Current vs. Gate2 to Source Voltage



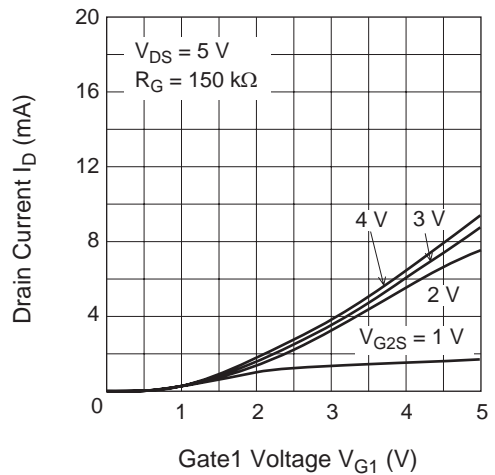
Drain Current vs. Gate1 Voltage



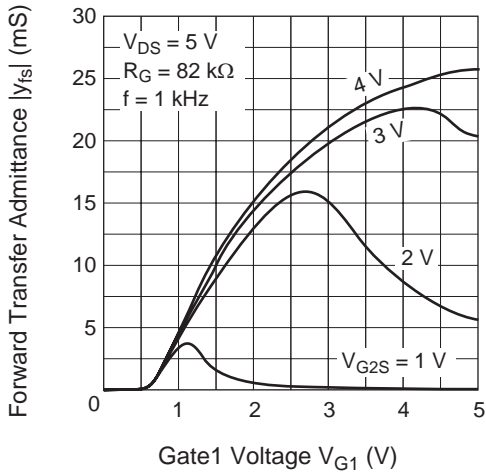
Drain Current vs. Gate1 Voltage



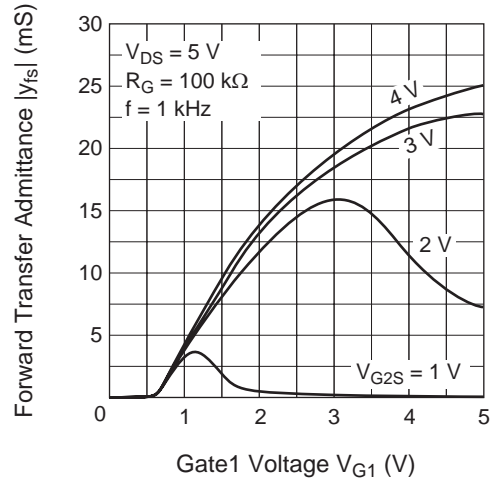
Drain Current vs. Gate1 Voltage



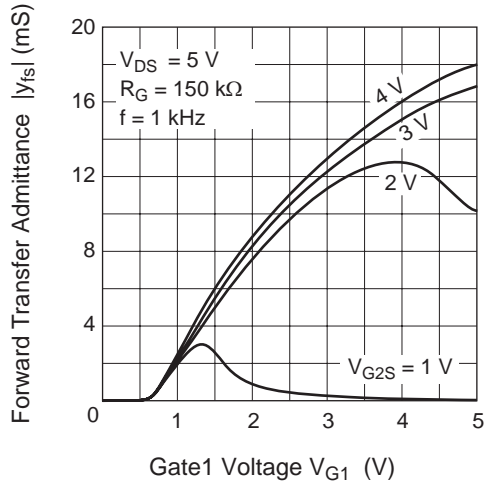
Forward Transfer Admittance vs. Gate1 Voltage



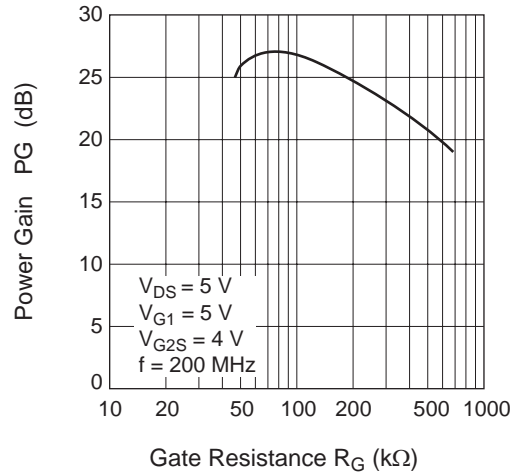
Forward Transfer Admittance vs. Gate1 Voltage



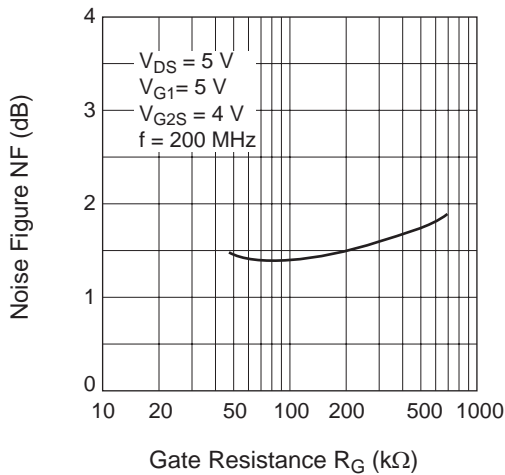
Forward Transfer Admittance vs. Gate1 Voltage



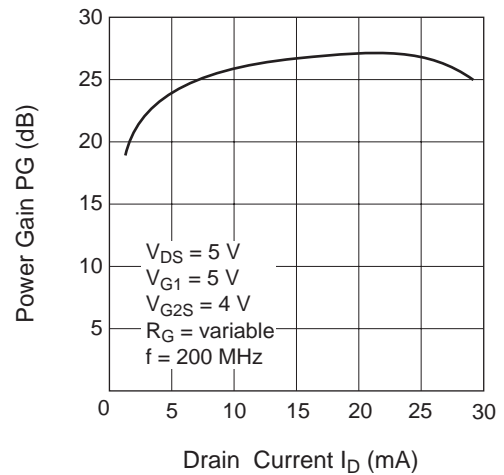
Power Gain vs. Gate Resistance



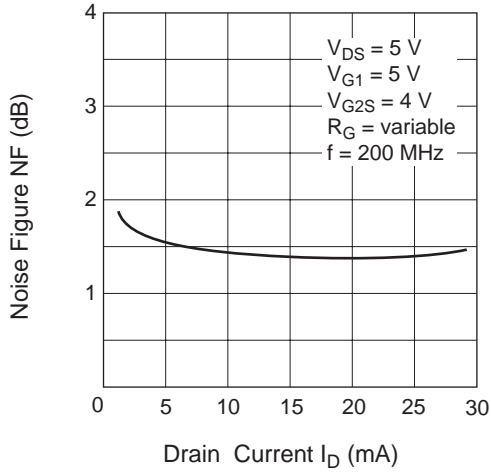
Noise Figure vs. Gate Resistance



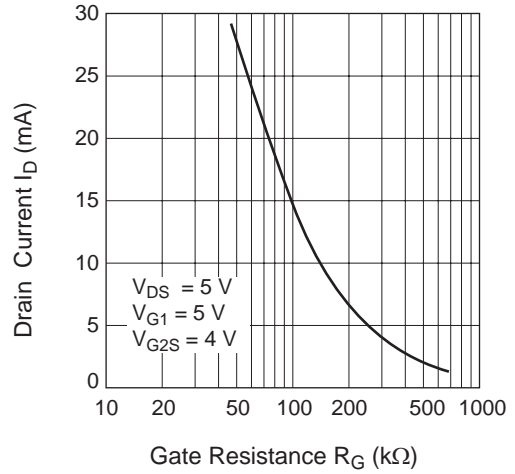
Power Gain vs. Drain Current



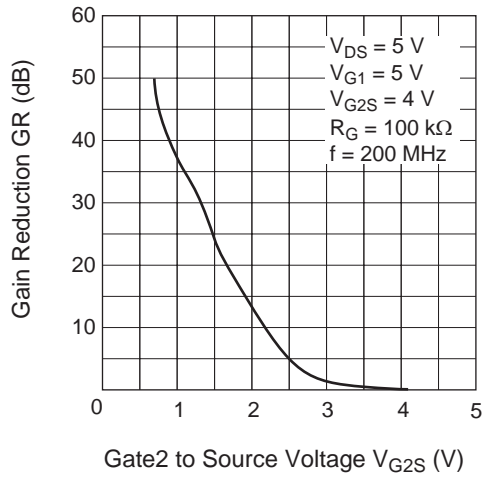
Noise Figure vs. Drain Current



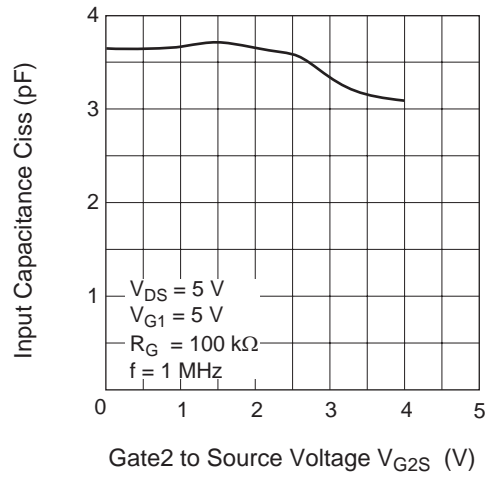
Drain Current vs. Gate Resistance



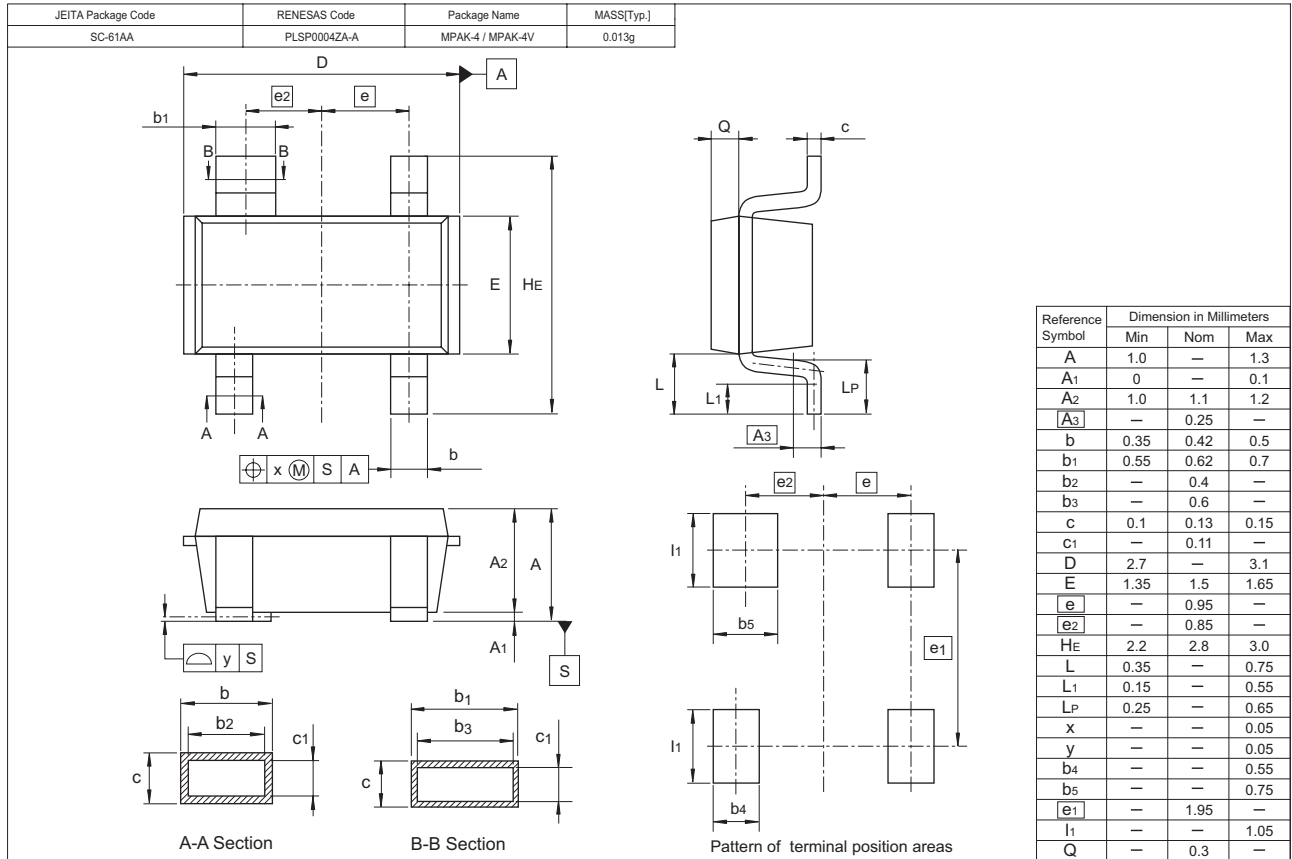
Gain Reduction vs. Gate2 to Source Voltage



Input Capacitance vs. Gate2 to Source Voltage



### Package Dimensions



### Ordering Information

Part Name	Quantity	Shipping Container
BB301MAW-TL-E	3000	φ 178 mm Reel, 8 mm Emboss Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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